

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

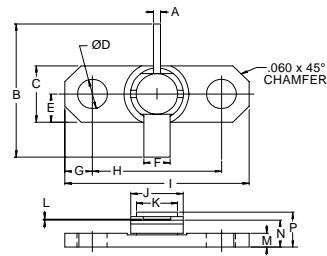
The **ASI MSC80914** is Designed for Class C, Common Base General Purpose Applications to 2.3 GHz.

**FEATURES INCLUDE:**

- Gold Metalization
- Site Emitter Ballasting

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	200 mA
<b>V<sub>CC</sub></b>	35 V
<b>P<sub>DISS</sub></b>	7.0 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-55 °C to +200 °C
<b>T<sub>STG</sub></b>	-55 °C to +200 °C
<b>θ<sub>JC</sub></b>	20 °C/W

**PACKAGE STYLE .250 2L FLG**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.028 / 0.71	.032 / 0.81
B	.740 / 18.80	
C	.245 / 6.22	.255 / 6.48
D	.128 / 3.25	.132 / 3.35
E		.125 / 3.18
F	.110 / 2.79	.117 / 2.97
G		.117 / 2.97
H	.560 / 14.22	.570 / 14.48
I	.790 / 20.07	.810 / 20.57
J	.225 / 5.72	.235 / 5.97
K	.165 / 4.19	.185 / 4.70
L	.003 / 0.08	.007 / 0.18
M	.058 / 1.47	.068 / 1.73
N	.119 / 3.02	.135 / 3.43
P	.149 / 3.78	.187 / 4.75

**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CBO</sub></b>	I <sub>C</sub> = 1.0 mA	45			<b>V</b>
<b>BV<sub>CER</sub></b>	I <sub>C</sub> = 5.0 mA    R <sub>BE</sub> = 10 Ω	45			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 1.0 mA	3.5			<b>V</b>
<b>I<sub>CBO</sub></b>	V <sub>CB</sub> = 28 V			0.5	<b>mA</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V    I <sub>C</sub> = 100 mA	15		150	<b>---</b>
<b>C<sub>ob</sub></b>	V <sub>CB</sub> = 28 V    f = 1.0 MHz		3.0	3.5	<b>pF</b>
<b>P<sub>out</sub></b>	V <sub>CC</sub> = 28 V    P <sub>in</sub> = 200 mW    fo = 2.0 GHz	1.0	1.25		<b>W</b>
<b>P<sub>G</sub></b>		7.0	8.0		<b>dB</b>
<b>η<sub>c</sub></b>		35	40		<b>%</b>